Japan Silicon Wafer Committee
Meeting Summary and Minutes

SEMICON Japan 2012
6th December 2012,13:00-17:00
Makuhari Messe, Chiba, Japan

Next Committee Meeting
8th March 2013, 13:00-17:00 Japan Standard Time
Japan Standards Spring Meeting 2013, Tokyo, Japan

Committee Announcements (optional)

Table 1 Meeting Attendees

Co-Chairs: Naoyuki J. Kawai (The University of Tokyo), Tetsuya Nakai (SUMCO)
SEMI Staff: Hirofumi Kanno

Company	*Last*	*First*	*Company*	*Last*	*First*
The University of Tokyo	Kawai	Naoyuki	SUMCO	Nakai	Tetsuya
Siltronic	Passek	Friedrich	Consutant	Takenaka	Takao
Kobelco Research Institute	Sumie	Shingo	Kuroda Precision	Naoi	Kaoru
Covalent Silicon	Takeda	Ryuji	KLA-Tencor	Shinha	Jaydeep
Sinton Instruments	Sinton	Ron	Raytex	Akiyama	Satoshi
Intel	Goldstein	Mike	Consultant	Shimizu	Yasuhiro
Self	Yoshise	Masanori	ELPIDA	Inoue	Michio
Shin-Etsu Handotai	Ohtsuki	Tsuyoshi	Consultant	Kumai	Sadao

Table 2 Leadership Changes

Group	*Previous Leader*	*New Leader*
Japan Test Method Task Force		Ryuji Takeda / Covalent Silicon
		Tsuyoshi Ohtsuki / Shin-Etsu Handotai
		Yoshimi Shiramizu / Renesus Electronics

Table 3 Ballot Results (or move to Section 4, Ballot Review)

Passed ballots and line items will be submitted to the ISC Audit & Review Subcommittee for procedural review.
Failed ballots and line items were returned to the originating task forces for re-work and re-balloting.

Document #	*Document Title*	*Committee Action*
5252A	Revision of SEMI M57-1011 with Title Change To: Specifications for Silicon Annealed Wafers	**Passed** with editorial changes
5442	Reapproval of SEMI M74-1108, Specification for 450 mm Diameter Mechanical Handling Polished Wafers	**Passed** as balloted (Super clean)
5441	Line Items Revision of SEMI M1-0812, Specifications for Polished Single Crystal Silicon Wafers	See below.
Line Item 1	This line item includes all changes in Section 2.6 of Table 1 (including addition of two new footnotes), in ¶¶ 6.6 through 6.6.3.4 including rearrangement of Tables 3 through 11, and in ¶ R4-7.5 as well as removal of Appendix 3 and addition of Related Information 2.	**Passed**
Line Item 2	This line item includes only removal of § 7	**Passed** as balloted (Super clean)

Table 3 Ballot Results (or move to Section 4, Ballot Review)

Passed ballots and line items will be submitted to the ISC Audit & Review Subcommittee for procedural review.
Failed ballots and line items were returned to the originating task forces for re-work and re-balloting.

Document #	*Document Title*	*Committee Action*
Line Item 3	This line item includes all other changes in the document. (See ¶¶ 2.1, 3.1, R3-3.1, R4-7.6 (Note 1), R4-7.7 (including removal of Note 6), and Footnote 3; §§ A1-1, A2-1, A2-2, A3-1, R3-1, and R4-1.)	**Passed** as balloted (Super clean)
5448	Revision of SEMI MF1528-0308, Test Method for Measuring Boron Contamination in Heavily Doped N-Type Silicon Substrates by Secondary Ion Mass Spectrometry	**Passed** as balloted (Super clean)
5449	Reapproval of SEMI MF1049-0308, Practice for Shallow Etch Pit Detection on Silicon Wafers	**Passed** as balloted (Super clean)
5451	Reapproval of SEMI MF1366-0308, Test Method for Measuring Oxygen Concentration in Heavily Doped Silicon Substrates by Secondary Ion Mass Spectrometry	**Passed** as balloted (Super clean)
5313B	Line Item Revisions of SEMI MF1535-0707, Test Method for Carrier Recombination Lifetime in Silicon Wafers by Noncontact Measurement of Photoconductivity Decay by Microwave Reflectance	See below.
Line Item 1	Changes to ¶1.3	**Failed**
Line Item 2	Renumbering of certain paragraphs and notes in §2 Scope, and correction to Note 1	**Failed**
Line Item 3	Addition of ¶3.8 and reference 7	**Failed**
Line Item 4	Corrections in ¶¶4.1, 5.1, 6.1.2, 6.1.3, 6.4, 7.2, 8.4, 11.3.2, and 13.1.6, Footnote 9, and the caption of Figure 3, and addition of reference 16 in §14	**Failed**
Line Item 5	Changes to Appendix 1	**Failed**
Line Item 6	Changes to Related Information 1	**Failed**
Line Item 7	Changes to Related Information 2	**Failed**
Line Item 8	Changes to Related Information 3	**Failed**
5389	Revision to MF1982-1110, Test Method for Analyzing Organic Contaminants on Silicon Wafer Surfaces by Thermal Desorption Gas Chromatography	**Failed** and returned to the Task Force for rework.
5424A	Line Items Revision to SEMI M62-0912, Specifications for Silicon Epitaxial Wafers	See below.
Line Item 1	Revision of Tables R2-7 & R2-8 - Change ¶3-1.7	**Passed** as balloted (Super clean)
Line Item 2	Revision of Tables R2-7 & R2-8 - Change ¶3-2.7 and explanation #9	**Failed** and returned to the Task Force for rework.
5450	Revision to SEMI M49-0912, Guide for Specifying Geometry Measurement Systems for Silicon Wafers for the 130 nm to 22 nm Technology Generations with Title Change to: Guide for Specifying Geometry Measurement Systems for Silicon Wafers for the 130 nm to 16 nm Technology Generations	**Failed** and returned to the Task Force for rework.

Table 4 Authorized Ballots (or move to Section 7, New Business)

#	*When*	*SC/TF/WG*	*Details*
5450A	Cycle 1, 2013	International AWG Task Force	Revision to SEMI M49-0912, Guide for Specifying Geometry Measurement Systems for Silicon Wafers for the 130 nm to 22 nm Technology Generations with Title Change to: Guide for Specifying Geometry Measurement Systems for Silicon Wafers for the 130 nm to 16 nm Technology Generations
5430A	Cycle 1, 2013	International AWG Task Force	Revision to SEMI M73-0309, Test Methods for Extracting Relevant Characteristics from Measured Wafer Edge Profiles

Table 5 Authorized Activities (or move to Section 7, New Business)

#	Type	SC/TF/WG	Details
5542	SNARF	International Epitaxial Wafer Task Force	Line Items Revision to M62-0912, Specifications for Silicon Epitaxial Wafers
5541	SNARF	International SOI Task Force	Revision of SEMI M41-0707 Specification of Silicon-on-Insulator (SOI) for Power Device/ICs
5540	SNARF	International AWG Task Force	New Auxiliary Information, Illustration of Flatness and Shape Metrics for Silicon Wafers
5539	SNARF	International AWG Task Force	Revision of SEMI MF1390-0707 (Reapproved 0512) ,Test Method for Measuring Warp on Silicon Wafers by Automated Non-Contact Scanning
5503	Revised SNARF	International Advanced Surface Inspection Task Force	Line Items Revision to SEMI M52-0912 Guide for Specifying Scanning Surface Inspection Systems for Silicon Wafers for the 130 nm to 11 nm Technology Generations (Re: To add M80 in reference) Note, this is a revised SNARF approval.
	TFOF	Japan Test Method Task Force	

Note: SNARFs and TFOFs are available for review on the SEMI Web site at:
http://downloads.semi.org/web/wstdsbal.nsf/TFOFSNARF

Table 6 New Action Items (or move to Section 8, Action Item Review)

Item #	Assigned to	Details
120612-1	SEMI Staff	To submit modified SNARF for Revision of SEMI MF-1535-0707, Test Method for Carrier Recombination Lifetime in Silicon Wafers by Noncontact Measurement of Photoconductivity Decay by Microwave Reflectance to Silicon Wafer GCS to have approval in December.

Table 7 Previous Meeting Actions Items **(or move to Section 8, Action item Review)**

Item #	Assigned to	Details
091912-1	Ryuji Takeda	To submit TFOF for Japan Test Method Task Force at the next committee meeting. ➔ Closed
091912-2	SEMI Staff	To confirm Task Force leaders of Task Force member list status of each Task Forces → Open
091912-3	SEMI Staff	To forward Revision of Related Information 2 of M80 to Silicon Wafer and PI&C Joint GCS voters for Approval in accordance with Regulations →Closed

1 Welcome, Reminders, and Introductions

Naoyuki J. Kawai called the meeting to order at 13:00. The meeting reminders on antitrust issues, intellectual property issues and holding meetings with international attendance were reviewed. Attendees introduced themselves.

2 Review of Previous Meeting Minutes

The committee reviewed the minutes of the previous meeting.

Motion: Approval for the previous meeting minutes of the Silicon Wafer committee
By / 2nd: Tetsuya Nakai (SUMCO) / Jaydeep Shinha (KLA-Tencor)
Discussion: None
Vote: 9:0

Attachment: 01, JA SW Minutes091912r2

3 Technical Committee Award

The Japan Silicon Wafer Commitee gave the Technical Committee Awards to Ryuji Takeda (GlobalWafers Japan) and Tsuyoshi Otsuki (Shin-Etsu Handotai).

4 Liaison Reports

4.1 JRSC Reports

Naoyuki J. Kawai (The university of Tokyo) reported that Naoyuki J. Kawai has been newly appointed as a JRSC co-chiar.

4.2 *Europe Silicon Wafer Committee*

Friedrich Passek (Siltronic) reported for the Europe Silicon Wafer Committee. Of note:

- Leadership Changes
  - Friedrich Passek stepped in
- New SNARF Approval
  - New Standard Specification for Polished Single Crystal Silicon Wafers for GaN-on-Silicon Applications
- Authorized ballots for cycle 1
  - Doc 5430A (Revision to SEMI M73-0309, Test Methods for Extracting Relevant Characteristics from Measured Wafer Edge Profiles)
  - Doc 5500 (New Standard Specification for Polished Single Crystal Silicon Wafers for GaN-on-Silicon Applications)
- Recent Meetings
  - SEMICON Europa, 8-12 October 2012, Dresden, Germany

Attachment: 02, ERSC Liaison Report Nov 2012

4.3 *North America Silicon Wafer Committee*

Jaydeep Shinha (KLA Tencor) reported for the North America Silicon Wafer Committee. Of note:

- Meeting Information
  - Last meeting: Tuesday, October 30, 2012, NA Fall Standards Meeting, Intel in Santa Clara, CA
  - Next meeting: Tuesday, April 2, 2013, NA Spring Standards Meeting, San Jose/Santa Clara, CA
- New SNARFs

- Int'l ASI TF
  - Doc. 5503, Line Item Revision to SEMI M52-0912 Guide for Specifying Scanning Surface Inspection Systems for Silicon Wafers for the 130 nm to 11 nm Technology Generations
    - To add M80, Mechanical Specification for Front-Opening Shipping Box Used to Transport and Ship 450 mm Wafers, in reference

- Ballots for Cycle 1-2013 (will be adjudicated in SEMICON West 2013)
  - Doc. 5503, Line Item Revision to SEMI M52-0912 Guide for Specifying Scanning Surface Inspection Systems for Silicon Wafers for the 130 nm to 11 nm Technology Generations
    - (Re: To add M80 in reference)

Attachment: 03, NA Si Wafer Liaison Report 20121116

4.4 *Silicon Wafer GCS*

Naoyuki J. Kawai (The University of Tokyo) reported for the Silicon Wafer GCS. Of note:

- In case document is end of its lifetime, Line Item ballot is not allowed, full revision is necessary for continuing or withdrawal or revision.
- In case of Line Item ballot, the consensus accordance with PG 3.5.1 in the Int'l Task Force is necessary.
- Task Force leader should keep the Task Force member list and invite actively to International meeting to get all information.

Attachment: 04, Silicon Wafer GCS Meeting_120612

4.5 JEITA Report

Naoyuki J. Kawai (The University of Tokyo) reported for the JEITA Silicon Wafer Committee. For details, these can be found at the New Business section of these minutes below.

4.6 *SEMI Staff Report*

Hirofumi Kanno (SEMI) gave the SEMI Staff Report. Of note:

- SEMI Global 2012-2013 Calendar of Events
- SEMICON Japan 2012
- 2012 Critical Dates for SEMI Standards Ballots
- Regulation SC
- A&R SC
- SEMI Standards Publication
- New Standards Ballot and Membership Systems
- New Ballot Formatting Templates
- Style Manual and Compilation of Terms
- Contact Information

Attachment: 05, SEMI Staff Report 2012 December R0.2

5 Ballot Review

5.1 Document # 5252A, Revision of SEMI M57-1011 with Title Change To: Specifications for Silicon Annealed Wafers

- Document passed technical review with editorial changes and was forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

Attachment: 06, 5252A_Ballot Review Sheet_r1

5.2 Document # 5442, Reapproval of SEMI M74-1108, Specification for 450 mm Diameter Mechanical Handling Polished Wafers

- Document passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

Attachment: 07, 5442_Ballot Review Sheet(Reapproval)

5.3 Document # 5441 Line Items Revision of SEMI M1-0812, Specifications for Polished Single Crystal Silicon Wafers

5.3.1 Line Item 1, This line item includes all changes in Section 2.6 of Table 1 (including addition of two new footnotes), in ¶¶ 6.6 through 6.6.3.4 including rearrangement of Tables 3 through 11, and in ¶ R4-7.5 as well as removal of Appendix 3 and addition of Related Information 2.

- The Line Item passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

5.3.2 Line Item 2, This line item includes only removal of § 7

- Document passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

5.3.3 Line Item 3, This line item includes all other changes in the document. (See ¶¶ 2.1, 3.1, R3-3.1, R4-7.6 (Note 1), R4-7.7 (including removal of Note 6), and Footnote 3; §§ A1-1, A2-1, A2-2, A3-1, R3-1, and R4-1.)

- Document passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

Attachment: 08, 5441_Ballot Review Sheet(LIs)_r2

5.4 Document # 5448, Revision of SEMI MF1528-0308, Test Method for Measuring Boron Contamination in Heavily Doped N-Type Silicon Substrates by Secondary Ion Mass Spectrometry

- Document passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

Attachment: 09, 5448_Ballot Review Sheet_SuperClean

5.5 Document # 5449 Reapproval of SEMI MF1049-0308, Practice for Shallow Etch Pit Detection on Silicon Wafers

- Document passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

Attachment: 10, 5449_Ballot Review Sheet_SuperClean

5.6 Document # 5451 Reapproval of SEMI MF1366-0308, Test Method for Measuring Oxygen Concentration in Heavily Doped Silicon Substrates by Secondary Ion Mass Spectrometry

- Document passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

Attachment: 11, 5451_Ballot Review Sheet SuperClean

5.7 Document # 5313B Line Item Revisions of SEMI MF1535-0707, Test Method for Carrier Recombination Lifetime in Silicon Wafers by Noncontact Measurement of Photoconductivity Decay by Microwave Reflectance

5.7.1 Line Item 1, Changes to ¶1.3

- The document failed technical review.

5.7.2 Line Item 2, Renumbering of certain paragraphs and notes in §2 Scope, and correction to Note 1

- The document failed technical review.

5.7.3 Line Item 3, Addition of ¶3.8 and reference 7

- The document failed technical review.

5.7.4 Line Item 4, Corrections in ¶¶4.1, 5.1, 6.1.2, 6.1.3, 6.4, 7.2, 8.4, 11.3.2, and 13.1.6, Footnote 9, and the caption of Figure 3, and addition of reference 16 in §14

- The document failed technical review.

5.7.5 Line Item 5, Changes to Appendix 1

- The document failed technical review.

5.7.6 Line Item 6, Changes to Related Information 1

- The document failed technical review.

5.7.7 Line Item 7, Changes to Related Information 2

- The document failed technical review.

5.7.8 Line Item 8, Changes to Related Information 3

- The document failed technical review.

Attachment: 12, 5313B_Ballot Review Sheet_LIs_r1

5.8 Document # 5389 Revision to MF1982-1110, Test Method for Analyzing Organic Contaminants on Silicon Wafer Surfaces by Thermal Desorption Gas Chromatography

- The document failed technical review and was back to the Test Methods task force for rework and reballot.

Attachment: 13, 5389_Ballot Review Sheet_r2

5.9 Document # 5424A Line Items Revision to SEMI M62-0912, Specifications for Silicon Epitaxial Wafers

5.9.1 Line Item 1, Revision of Tables R2-7 & R2-8 - Change ¶3-1.7

- Document passed technical review as balloted and forwarded to the ISC Audits and Reviews Subcommittee for procedural review. See attachment below for detail of ballot adjudication.

5.9.2 Line Item 2, Revision of Tables R2-7 & R2-8 - Change ¶3-2.7 and explanation #9

- The document failed technical review and was back to the Test Methods task force for rework and reballot.

5.10 Document # 5450 Revision to SEMI M49-0912, Guide for Specifying Geometry Measurement Systems for Silicon Wafers for the 130 nm to 22 nm Technology Generations with Title Change to: Guide for Specifying Geometry Measurement Systems for Silicon Wafers for the 130 nm to 16 nm Technology Generations

- The document failed technical review and was back to the Test Methods task force for rework and reballot.

Attachment: 14, 5450_Ballot Review Sheet_r2

NOTICE: This document met the 90% approval condition set forth in Section 9.6.3 of the *Regulations Governing SEMI Standards Committees* at the close of balloting.

NOTICE: This document did NOT meet the 90% approval condition set forth in Section 9.6.3 of the *Regulations Governing SEMI Standards Committees* at the close of balloting.

6 Subcommittee & Task Force Reports

6.1 International Polished Wafers Task Force

Takao Takenaka (Consultant) reported for the International Polished Wafers Task Force. This report contained information below.

- Revision to M1 : To develop a modification of nanotopography value and related foot note in Table R1-1.

Schedule is to develop SNARF in December, circulate to GCS, and ballot in cycle 1 or 2.

- Revision to M1 : To simplify the parameter based edge profile specification.

A plan is to develop a SNARF to cover the changes suggested by John Valley and Peter Wager as balloting Doc.5441 and should simplify M1 even further. This is likely to be controversial, a plan is to present this together with a proposed draft at the NA spring meetings and ballot before West 2013 (cycle 3 or 4) so it could be adjudicated there. However, it may take longer than that to get consensus, so the schedule is only an optimistic one.

Both of the revisions to M1 proposed by M. Bullis were discussed and accepted to be explained.

Attachment: 15, Minutes of IPW TF Meeting on Dec.4, 2012

6.2 International Epitaxial Wafers Task Force

Takao Takenaka (Consutant) reported for the International Epitaxial Wafers Task Force. A New SNARF was proposed by Takao Takenaka.

Motion: Approval for New SNARF (Doc.5542) for Line Items Revision to M62-0912, Specifications for Silicon Epitaxial Wafers

By / 2nd: Takao Takenaka (Consutant) / Friedrich Passek (Siltronic)

Discussion: None

Vote: 10:0

Doc. 5542 above is going to be adjudicated at North America Silicon Wafer Committee meeting at SEMICON West 2013.

Attachment: 16, Minutes of IEpiW TF Meeting on Dec.4, 2012

6.3 International Annealed Wafers Task Force

Rryuji Takeda (Covalent Silicon) reported for the International Annealed Wafers Task Force instead of Koji Izunome. This report contained information on .

Attachment: 17, Doc 5252A Ballot Results 103012

6.4 International SOI Wafers Task Force

Tetsuya Nakai (SUMCO) reported for the SOI Task Force. This report contained information on .

As for SEMI M41, in section 3, Referenced Standard and documents, SEMI M34 (Guide for Specifying SIMOX Wafers) has been withdrawn and SEMI M71 (Specification for Silicon-on-Insulator (SOI) Wafers for CMOS LSI) was published in 2010 (revised 2012). The Task Force members decided to work for removal of SEMI M34 and add SEMI M71 for referenced standard in SEMI M41.

Motion: Approval for New SNARF (Doc. 5541) for Revision of SEMI M41-0707 Specification of Silicon-on-Insulator (SOI) for Power Device/ICs

By / 2nd: Tetsuya Nakai (SUMCO) / Masanori Yoshise (Self)

Discussion: None

Vote: 10:0

Doc. 5541 above will be issued in cycle 4 and adjudicated at SEMICON West 2013.

Attachment: 18, SOI TF Report_121206

6.5 Reclaim Wafer Task Force

Takao Takenaka (Consultant) reported that there was no update for the Reclaim Wafer Task Force.

6.6 International Terminology Task Force

Tetsuya Nakai (SUMCO) reported that there was no update for the International Terminology Task Force.

6.7 International Test Methods Task Force

Ryuji Takeda (Covalent Silicon) reported for the International Test Methods Task Force. This report contained information below.

The SNARF for *Revision of SEMI MF-1535-0707, Test Method for Carrier Recombination Lifetime in Silicon Wafers by Noncontact Measurement of Photoconductivity Decay by Microwave Reflectance* will be submitted to Silicon Wafer GCS in December.

Action Item: 120612-01, To submit modified SNARF for Revision of SEMI MF-1535-0707, Test Method for Carrier Recombination Lifetime in Silicon Wafers by Noncontact Measurement of Photoconductivity Decay by Microwave Reflectance to Silicon Wafer GCS to have approval in December. (SEMI Staff)

Attachment: 19, SintonPresentation

Attachment: 19-1, SNARF Revision1535_r2

6.8 Japan Test Method Task Force

Ryuji Takeda (Covalent Silicon) reported for the Japan Test Method Task Force. This report contained information on .

- GOI Working Group (Otsuki-san)

For M60 Revision, Test Method for Time Dependent Dielectric Breakdown Characteristics of SiO2 Films for Si Wafer Evaluation, the Task Force reformatted to be compliant with the current SEMI Style Manual. In 2013 Spring, this document will be ballot.

- Surface Organic Contaminant Analysis Working Group (Shiramizu-san)

The Task Force reported to develop Doc. 5389A, Revision to MF1982-1110, Test Method for Analyzing Organic Contaminants on Silicon Wafer Surfaces by Thermal Desorption Gas Chromatography.

- Surface Metal Chemical Analysis Working Group (Takeda-san/ Torayama-san)

For Doc.4844B, Guide for the Measurement of Trace Metal Contamination on Silicon Wafer Surface by Inductively Coupled Plasma Mass Spectrometry, the Task Force has done more discussion about“Method Blank” with EU authority. The document will be submitted in spring 2013.

- Bulk Heavy Metal Analysis by Electrical Measurement Working Group (Sumie-san)

The Task Force reported to develop 5313C, Line Item Revisions of SEMI MF1535-0707, Test Method for Carrier Recombination Lifetime in Silicon Wafers by Noncontact Measurement of Photoconductivity Decay by Microwave Reflectance

- BMD DZ Working Group (Akiyama-san/ Moriya-san)

No update

Ryuji Takeda submitted TFOF for Japan Test Method Task Force.

Motion: Approval for TFOF for Japan Test Method Task Force
By / 2nd: Ryuji Takeda (Covalent Silicon) / Tsuyoshi Ohtsuki (Shin-Etsu Handotai)
Discussion: None
Vote: 6:4

Attachment: 20, Test method TF Progress Report(GOI)(121206) for Silicon Wf Commite_rev2(E)

6.9 International 450mm Shipping Box Task Force / JA Shipping Box Task Force

Yasuhiro Shimizu (Consultant) reported for the International 450mm Shipping Box Task Force and JA Shipping Box Task Force. This report contained information on the result of revision of 450 FOSB SEMI M80-1111 and 450 mm wafer shipping system under development.

Attachment: 21, SHIPPING BOX TF REPORT 2012_12_07

6.10 International 450mm Wafer Task Force

Mike Goldstein (Intel) reported for the International 450 mm Wafer Task Force. This report contained information on the ballot result for doc. 5442, Reapproval of SEMI M74-1108, Specification for 450 mm Diameter Mechanical Handling Polished Wafers. .

6.11 International Advanced Wafer Geometry Task Force/ Japan AWG Task Force

Masanori Yoshise (Self) reported for the International Advanced Wafer Geometry Task Force/ Japan AWG Task Force.

- New standard for Test Method for geometry parameter.

Following us NA Fall meeting, TF discussed revised Test Method Standard such as MF 1390, MF1451, MF1540 which are not meet current metrology Specially Test Method of Bow measurement is not "Non Contact and Automated" TF agreed to develop new document for Bow

- Development geometry definition with figure illustration.

TF agreed to create working group for improved geometry definition with figure illustration as auxiliary document of M1 or so. The working group candidates were Murray, John Valley, Peter Wagner Yoshise

The Task Force proposed Doc. 5450A.

Motion: Approval for Doc. 5450A ballot submission in Cycle1-2013
By / 2nd: Masanori Yoshise (Self) / Jaydeep Shinha (KLA Tencor)
Discussion: None

Vote: 10:0

Motion: Doc. 5450A asks GCS agreement overwrite Silicon Wafer International Meeting rule but to be adjudicated at NA Spring Meeting.
By / 2nd: Masanori Yoshise (Self) / Tetsuya Akiyama (Raytex)
Discussion: None
Vote: 10:0

The Task Force also proposed Doc. 5430A.

Motion: Approval for Doc. 5430A ballot submission in Cycle1-2013
By / 2nd: Masanori Yoshise (Self) / Friedrich Passek (Siltronic)
Discussion: None
Vote: 10:0

Motion: Approval for SNARF (Doc.5540) for: New Auxiliary Information, Illustration of Flatness and Shape Metrics for Silicon Wafers
By / 2nd: Masanori Yoshise (Self) / Friedrich Passek (Siltronic)
Discussion: None
Vote: 10:0

Motion: Approval for Revised SNARF(Doc.5503) for: Revised MF1390, Test Method for Measuring Warp on Silicon Wafer by Automated non-contact scanning
By / 2nd: Masanori Yoshise (Self) / Tetsuya Akiyama (Raytex)
Discussion: None
Vote: 10:0

Attachment: 22, 20121204 AWG TF Meeting Minutes

6.12 International Advanced Surface Inspection Task Force

Friedrich Passek (Siltronic) reported for the International Advanced Surface Inspection Task Force. This report contained information on .

Motion: Approval for modified SNARF (Doc. 5503) for Line Item Revision to SEMI M52-0912 Guide for Specifying Scanning Surface Inspection Systems for Silicon Wafers for the 130 nm to 11 nm Technology Generations (Re: To add M80 in reference)
By / 2nd: Friedrich Passek (Siltronic), Tetsuya Nakai (SUMCO)
Discussion: None
Vote: 9:0

7 Old Business

7.1 Previous Action Item

Hirofumi Kanno addressed the committee on this topic.

8 New Business

8.1 STEP/450 during SEMICON Japan 2012

Hirofumi Kanno addressed the committee on this topic.

8.2 Transfer of JEITA Standards

Naoyuki J. Kawai addressed the committee of this topic.

Attachment: 23, JEITA Liason Report

8.3 GCS should discuss how to deal with close to end of life standard(e.g. M74, M76)

Friedrich Passek addressed the committee of this topic.

9 Action Item Review

9.1 *Open Action Items*

Hirofumi Kanno (SEMI) reviewed the open action items. These can be found in the Open Action Items table at the beginning of these minutes.

9.2 *New Action Items*

Hirofumi Kanno (SEMI) reviewed the new action items. These can be found in the New Action Items table at the beginning of these minutes.

10 Next Meeting and Adjournment

The next meeting of the Japan Silicon Wafer committee is scheduled for Friday 8th March, 2013 at Japan Standards Spring Meetings 2013 in SEMI Japan office, Tokyo, Japan.

Respectfully submitted by:
Hirofumi Kanno
Senior Coordinator
SEMI Japan
Phone: +81.3.3222.5862
Email: hkanno@semi.org

Minutes approved by:

Naoyuki J. Kawai (The University of Tokyo), Co-chair	<Date approved>
Tetsuya Nakai (SUMCO), Co-chair	<Date approved>

Table 8 Index of Available Attachments [#1]

#	*Title*	#	*Title*
01	JA SW Minutes091912r2	14	5450_Ballot Review Sheet_r2
02	ERSC Liaison Report Nov 2012	15	Minutes of IPW TF Meeting on Dec.4, 2012
03	NA Si Wafer Liaison Report 20121116	16	Doc 5252A Ballot Results 103012
04	Silicon Wafer GCS Meeting_120612	17	Doc 5252A Ballot Results 103012
05	SEMI Staff Report 2012 December R0.2	18	SOI TF Report_121206
06	5252A_Ballot Review Sheet_r1	19	SintonPresentation
07	Ballot Review Sheet(Reapproval)	19-1	SNARF Revision1535_r2
08	5441_Ballot Review Sheet(LIs)_r2	20	Test method TF Progress Report(GOI)(121206) for Silicon Wf Commite_rev2(E)
09	5448_Ballot Review Sheet_SuperClean	21	SHIPPING BOX TF REPORT 2012_12_07
10	5449_Ballot Review Sheet_SuperClean	22	20121204 AWG TF Meeting Minutes
11	5451_Ballot Review Sheet SuperClean	23	JEITA Liason Report
12	5313B_Ballot Review Sheet_LIs_r1		
13	5389_Ballot Review Sheet_r2		

#1 Due to file size and delivery issues, attachments must be downloaded separately. A .zip file containing all attachments for these minutes is available at www.semi.org. For additional information or to obtain individual attachments, please contact [SEMI Staff Name] at the contact information above.